1.8V Drive Nch+Nch MOSFET

US6K4

●Structure

Silicon N-channel MOSFET

● Features

- 1) Two Nch MOSFETs are put in TUMT6 package.
- 2) High-speed switching, Low On-resistance.
- 3) 1.8V drive.

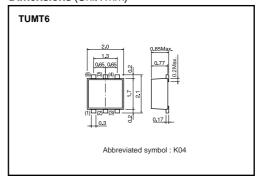
Applications

Switching

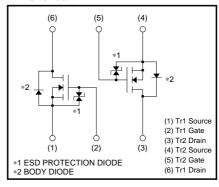
Packaging specifications

	Package	Taping		
Type	Code	TR		
	Basic ordering unit (pieces)	3000		
US6K4		0		

● **Dimensions** (Unit: mm)



●Inner circuit



● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2>

Parameter Drain-source voltage Gate-source voltage		Symbol	Limits	Unit	
		VDSS	20	V	
		V _{GSS}	±10	V	
Drain augrent	Continuous	I _D	±1.5	Α	
Drain current	Pulsed	I _{DP} *1	±3.0	Α	
Source current (Body diode)	Continuous	ls	0.6	Α	
	Pulsed	Isp *1	2.4	Α	
Total power dissipation		Pp *2	1.0	W / TOTAL	
		Гυ	0.7	W / ELEMENT	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tsta	-55 to +150	°C	

^{*1} Pw≤10μs, Duty cycle≤1%

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W / TOTAL
Charmer to ambient	Kill(Cli-a)	179	°C/W / ELEMENT

^{*} Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

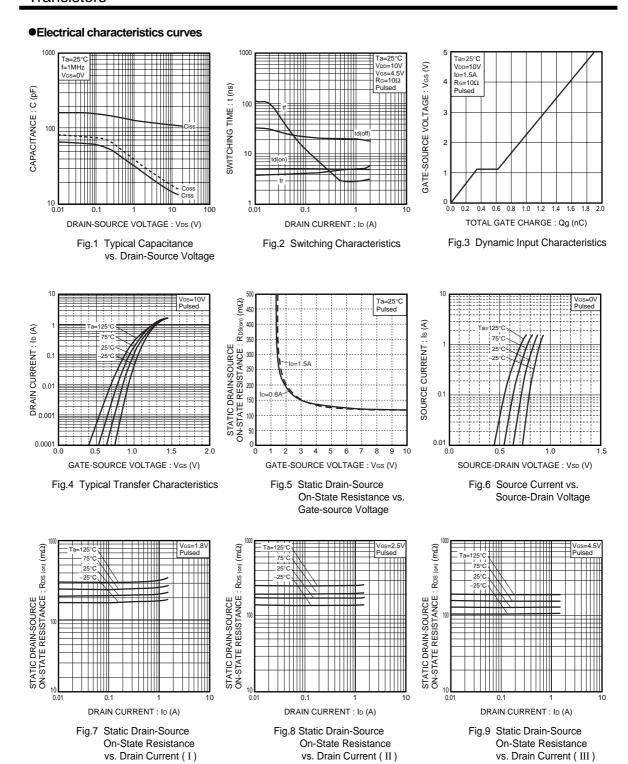
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	V _{GS} =±10V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	20	_	_	٧	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	_	1	μΑ	V _{DS} = 20V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	_	1.0	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance		1	130	180	mΩ	ID= 1.5A, VGS= 4.5V
	R _{DS (on)} *	-	170	240	mΩ	I _D = 1.5A, V _{GS} = 2.5V
		-	220	310	mΩ	I _D = 0.8A, V _{GS} = 1.8V
Forward transfer admittance	Y _{fs} *	1.6	-	-	S	V _{DS} = 10V, I _D = 1.5A
Input capacitance	Ciss	_	110	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	18	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	15	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	_	5	_	ns	ID= 1.0A
Rise time	tr *	_	5	_	ns	V _{DD} ≒ 10V
Turn-off delay time	t _{d (off)} *	_	20	_	ns	V_{GS} = 4.5V R_{L} = 10 Ω
Fall time	t _f *	_	3	_	ns	RGs= 10Ω
Total gate charge	Qg *	-	1.8	2.5	nC	V _{DD} ≒10V
Gate-source charge	Qgs *	_	0.3	_	nC	V _{GS} = 4.5V
Gate-drain charge	Q _{gd} *	_	0.3	_	nC	ID= 1.5A

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	-	1.2	٧	I _S = 0.6A, V _{GS} =0V



●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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